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SIDDHARTH INSTITUTE OF ENGINEERING & TECHNOLOGY:: PUTTUR
(AUTONOMOUS)
M.Tech I Year I Semester Regular Examinations July-2021
VLSI TECHNOLOGY
(VLSI)

Time: 3 hours

Max. Marks: 60

(Answer all Five Units 5 x 12 = 60 Marks)

UNIT-I

- 1 a Illustrate the main steps in a typical N-WELL process. L2 6M
 b Explain a Bi-CMOS inverter with a neat sketch. L2 6M

OR

- 2 Derive the relation between drain to source current I_{ds} VS drain to source voltage V_{ds} in non-saturated and saturated. L4 12M

UNIT-II

- 3 a What are the different strategies for building low power gates? Explain. L1 6M
 b Differentiate switch logic and gate logic. L4 6M

OR

- 4 a Explain clearly the Scalable design rules. L2 6M
 b Explain about static complementary gates. L2 6M

UNIT-III

- 5 a Draw the single row layout design. L2 6M
 b Briefly discuss about crosstalk minimization. L2 6M

OR

- 6 a Explain the clocking disciplines and power optimization in sequential systems. L2 6M
 b What are the various simulators used for combinational logic? L1 6M

UNIT-IV

- 7 a Briefly discuss about floor planning methods. L2 6M
 b Write short notes on design validation. L1 6M

OR

- 8 a Explain about placement and routing at chip level design. L2 6M
 b Explain about architecture testing. L2 6M

UNIT-V

- 9 a Explain about system on chips and embedded CPUs. L2 6M
 b Write notes on logic synthesis. L2 6M

OR

- 10 With a diagram explain about detailed routing method. L2 12M

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